

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VHB40-28F** is Designed for

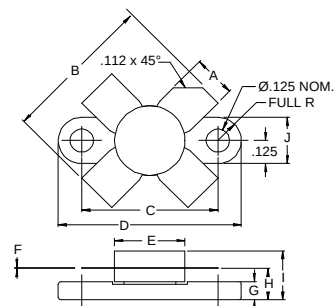
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	65 V
V_{CE0}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10726

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200\text{ mA}$	35			V
BV_{CES}	$I_C = 200\text{ mA}$	65			V
BV_{CBO}	$I_C = 10\text{ mA}$	65			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 30\text{ V}$			1.0	mA
I_{CES}	$V_{CE} = 30\text{ V}$			10	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	5.0		200	---
C_{ob}	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$			65	pF
P_G η_C	$V_{CE} = 28\text{ V}$ $P_{IN} = 7.0\text{ W}$ $f = 175\text{ MHz}$	7.6 60			dB %